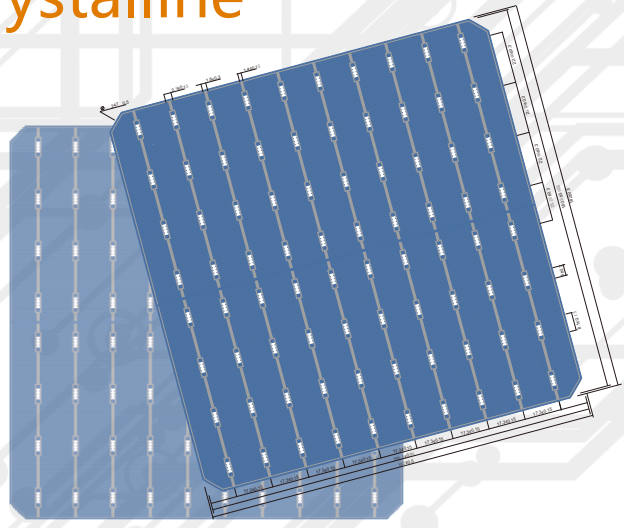
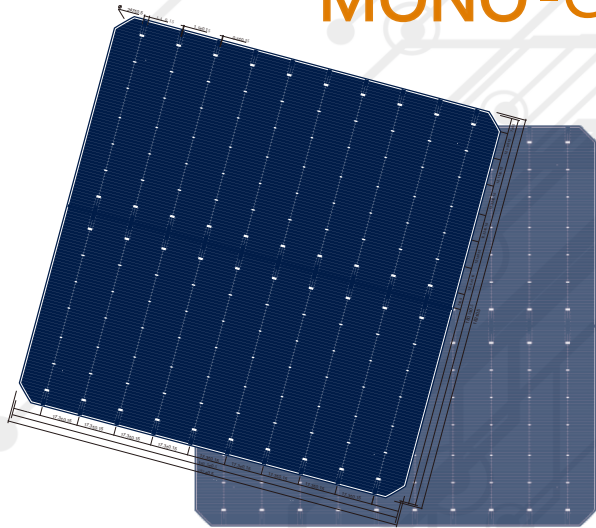


SGGS182M

MONO-Crystalline



Technical Data and Design

Dimension	182mmx182mm±0.5 247mm
Diameter	247mm±0.25mm
Thickness	190μm±30μm (Excluding positive silver thickness)
Front(-)	0.06mm wide main gate, 132 auxiliary gates, blue silicon nitride antireflection film
Back(+)	6 sections of 1.8mm silver pads are embedded in 1.4mm aluminum main grid and 182 aluminum auxiliary grids

Electrical Performance Parameters

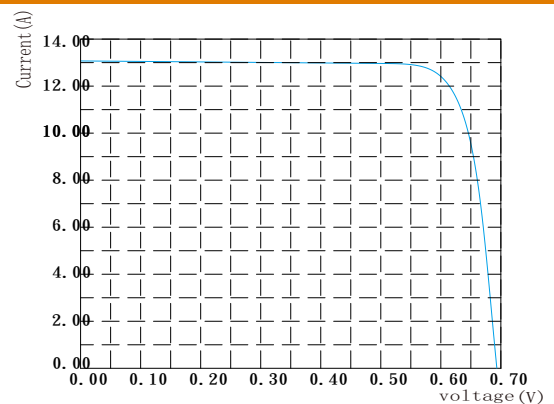
NCell (%)	Pmpp (W)	Vmp (V)	Imp (A)	Voc (V)	Isc (A)
22.3-23.0	7.59	0.5907	12.854	0.6904	13.521
22.90-23.0	7.56	0.5889	12.839	0.6884	13.505
22.80-22.90	7.53	0.5870	12.824	0.6864	13.489
22.70-22.80	7.49	0.5852	12.807	0.6854	13.472
22.60-22.70	7.46	0.5834	12.790	0.6836	13.454
22.50-22.60	7.43	0.5815	12.774	0.6827	13.437
22.40-22.50	7.40	0.5798	12.756	0.6818	13.418
22.30-22.40	7.36	0.5779	12.740	0.6801	13.401
22.20-22.30	7.33	0.5757	12.732	0.6783	13.393
22.10-22.20	7.30	0.5740	12.711	0.6782	13.371
22.00-22.10	7.26	0.5721	12.696	0.6772	13.355
21.90-22.00	7.23	0.5703	12.677	0.6763	13.335

Note: double sided rate(Back Pmpp/Front Pmpp,Back Isc/Front Isc)_{min}≥70%

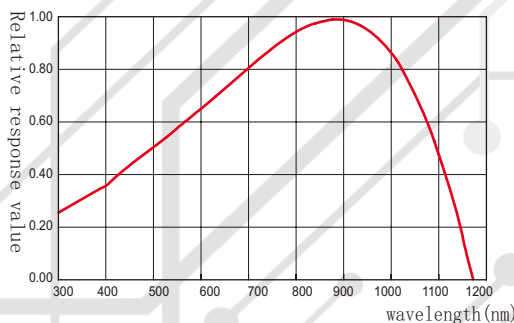
I-V characteristics under low illumination

Intensity [W/m ²]	Voc [%]	Isc [%]	Pmpo [%]
1000	100.00	100.00	100.00
800	99.10	80.08	80.24
600	97.84	60.00	59.99
400	96.22	40.00	39.68
200	93.32	19.98	19.30

IV Curve



Spectral response characteristics



Thermal Characteristics

PARAMETERS	UNIT	MEASUREMENT
α_{isc}	[%/°C]	0.060
β_{voc}	[%/°C]	-0.300
γ_{pmax}	[%/°C]	-0.390

The above datas are compiled based on the existing Gstar plant process and equipment conditions, and Gstar energy reserves the right of final interpretation.

Gstar

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